

ON Semiconductor

Is Now

The logo for onsemi, featuring the word "onsemi" in a dark teal, lowercase, sans-serif font. The letter "i" is stylized with a white dot and a teal vertical bar. A small orange triangle is positioned above the top right of the "i". A trademark symbol (TM) is located to the right of the logo.

To learn more about onsemi™, please visit our website at
www.onsemi.com

onsemi and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.

NTQD6968

Power MOSFET 6.6 Amps, 20 Volts N-Channel TSSOP-8

Features

- Ultra Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Logic Level Gate Drive
- Miniature Dual TSSOP-8 Surface Mount Package
- Diode Exhibits High Speed, Soft Recovery
- Micro8 Mounting Information Provided

Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Computers, Printers, PCMCIA Cards, Cellular and Cordless Telephones

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	20	Vdc
Gate-to-Source Voltage – Continuous	V_{GS}	± 12	Vdc
Drain Current – Continuous @ $T_A 25^\circ\text{C}$	I_D	5.4	Adc
– Continuous @ $T_A 70^\circ\text{C}$	I_D	4.5	
– Pulsed (Note 3)	I_{DM}	15	
Total Power Dissipation @ $T_A 25^\circ\text{C}$	P_D	0.94	W
Drain Current – Continuous @ $T_A 25^\circ\text{C}$	I_D	6.6	Adc
– Continuous @ $T_A 70^\circ\text{C}$	I_D	4.5	
– Pulsed (Note 3)	I_{DM}	20	
Total Power Dissipation @ $T_A 25^\circ\text{C}$	P_D	1.42	W
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 20 \text{ Vdc}$, $V_{GS} = 5.0 \text{ Vdc}$, Peak $I_L = 5.5 \text{ Apk}$, $L = 10 \text{ mH}$, $R_G = 25 \Omega$)	E_{AS}	150	mJ
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{\theta JA}$	132	$^\circ\text{C/W}$
Junction-to-Ambient (Note 2)		88	
Maximum Lead Temperature for Soldering Purposes for 10 seconds	TL	260	$^\circ\text{C}$

1. Minimum FR-4 or G-10 PCB, Steady State.
2. Mounted onto a 2" square FR-4 Board (1" sq. 2oz. Cu 0.06" thick single sided), Steady State.
3. Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2%.

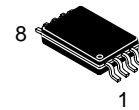
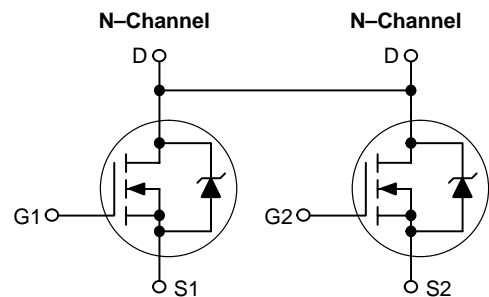


ON Semiconductor

<http://onsemi.com>

**6.6 AMPERES
20 VOLTS**

$R_{DS(on)} = 22 \text{ m}\Omega$



**TSSOP-8
CASE 948S
PLASTIC**

MARKING DIAGRAM & PIN ASSIGNMENT



Top View

968 = Device Code
Y = Year
WW = Work Week
N = MOSFET

ORDERING INFORMATION

Device	Package	Shipping
NTQD6968	TSSOP-8	100 Units/Rail
NTQD6968R2	TSSOP-8	3000/Tape & Reel

NTQD6968

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 250 μAdc) Temperature Coefficient (Positive)	V _{(BR)DSS}	20 –	– 12	– –	Vdc mV/°C
Zero Gate Voltage Collector Current (V _{DS} = 16 Vdc, V _{GS} = 0 Vdc, T _J = 25°C) (V _{DS} = 16 Vdc, V _{GS} = 0 Vdc, T _J = 125°C)	I _{DSS}	– –	– –	1.0 10	μAdc
Gate-Body Leakage Current (V _{GS} = ±12 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	–	–	±100	nAdc

ON CHARACTERISTICS

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 250 μAdc) Temperature Coefficient (Negative)	V _{GS(th)}	0.6 –	0.75 –2.5	1.2 –	Vdc mV/°C
Static Drain-to-Source On-State Resistance (V _{GS} = 4.5 Vdc, I _D = 6.6 Adc) (V _{GS} = 2.5 Vdc, I _D = 5.3 Adc) (V _{GS} = 2.5 Vdc, I _D = 3.3 Adc)	R _{DS(on)}	– – –	– – –	0.022 0.030 0.030	Ω
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 6.6 Adc)	g _{FS}	–	19.2	–	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 16 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	–	900	–	pF
Output Capacitance		C _{oss}	–	350	–	
Transfer Capacitance		C _{rss}	–	100	–	

SWITCHING CHARACTERISTICS (Notes 4 & 5)

Turn-On Delay Time	(V _{DD} = 16 Vdc, I _D = 6.6 Adc, V _{GS} = 4.5 Vdc, R _G = 6.0 Ω)	t _{d(on)}	–	9.0	–	ns
Rise Time		t _r	–	35	–	
Turn-Off Delay Time		t _{d(off)}	–	70	–	
Fall Time		t _f	–	70	–	
Gate Charge	(V _{DS} = 16 Vdc, V _{GS} = 4.5 Vdc, I _D = 6.6 Adc)	Q _{tot}	–	13.5	20	nC
	Q _{gs}	–	3.0	–		
	Q _{gd}	–	4.0	–		

BODY-DRAIN DIODE RATINGS (Note 4)

Forward On-Voltage	(I _S = 6.0 Adc, V _{GS} = 0 Vdc)	V _{SD}	–	–	1.2	Vdc
Reverse Recovery Time	(I _S = 6.15 Adc, V _{GS} = 0 Vdc, di _S /dt = 100 A/μs)	t _{rr}	–	30	–	ns
		t _a	–	19	–	
		t _b	–	15	–	
Reverse Recovery Stored Charge		Q _R	–	0.017	–	μC

4. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.
5. Switching characteristics are independent of operating junction temperature.

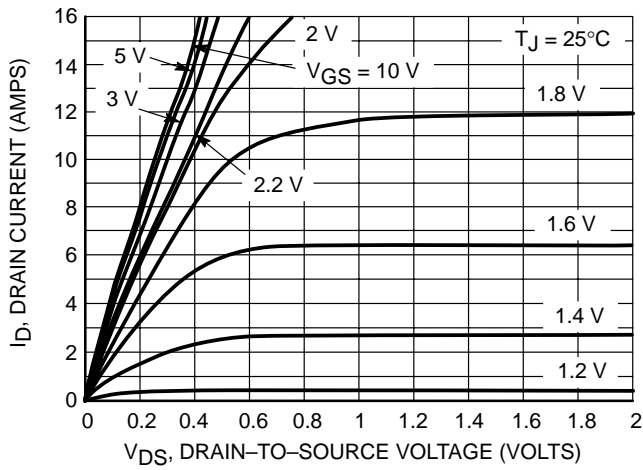


Figure 1. On-Region Characteristics

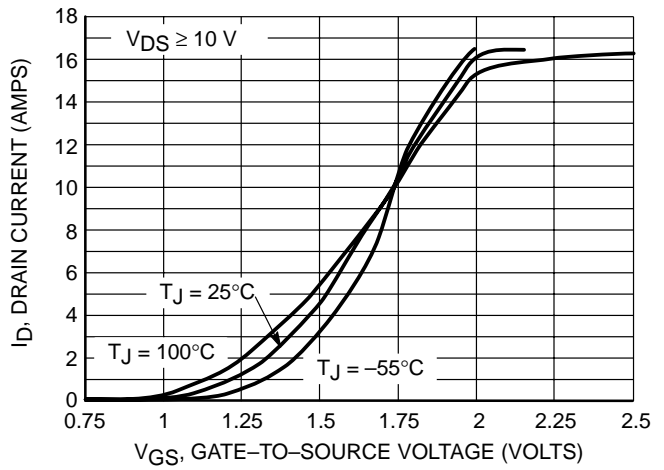


Figure 2. Transfer Characteristics

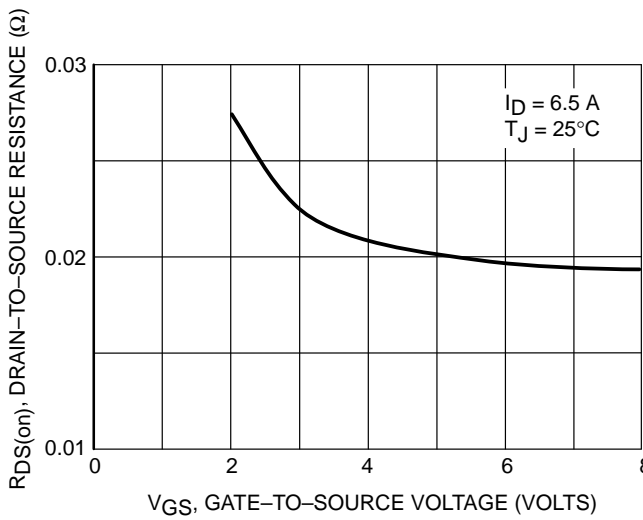


Figure 3. On-Resistance versus Gate-to-Source Voltage

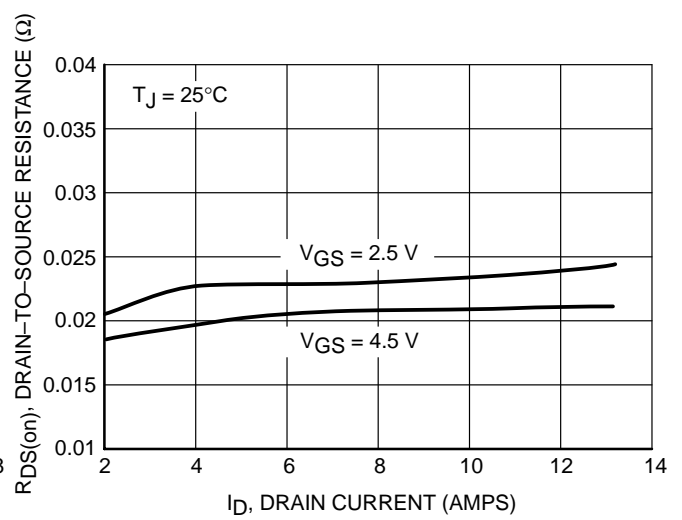


Figure 4. On-Resistance versus Drain Current and Gate Voltage

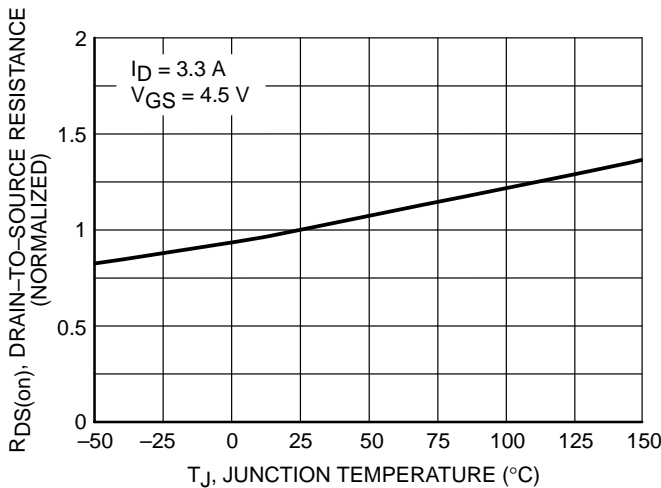


Figure 5. On-Resistance Variation with Temperature

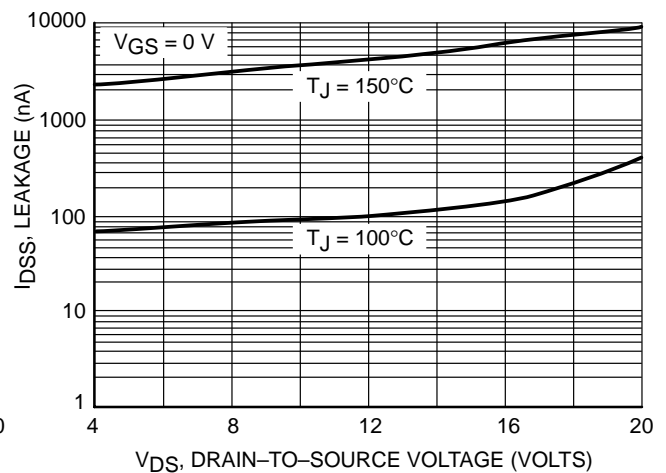


Figure 6. Drain-to-Source Leakage Current versus Voltage

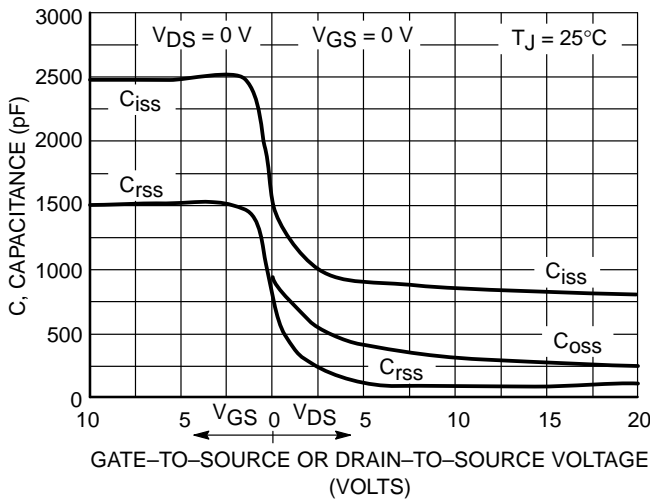


Figure 7. Capacitance Variation

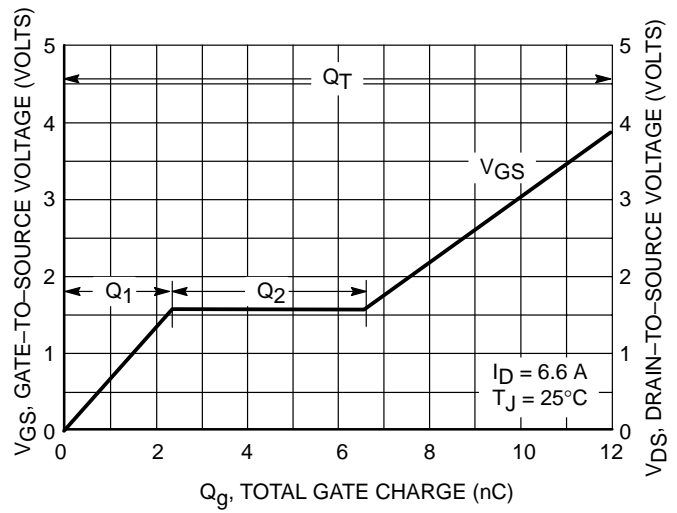


Figure 8. Gate-to-Source Voltage versus Total Charge

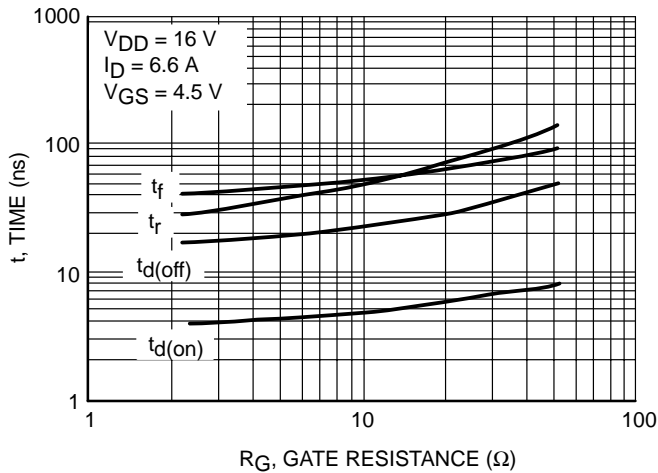


Figure 9. Resistive Switching Time Variation versus Gate Resistance

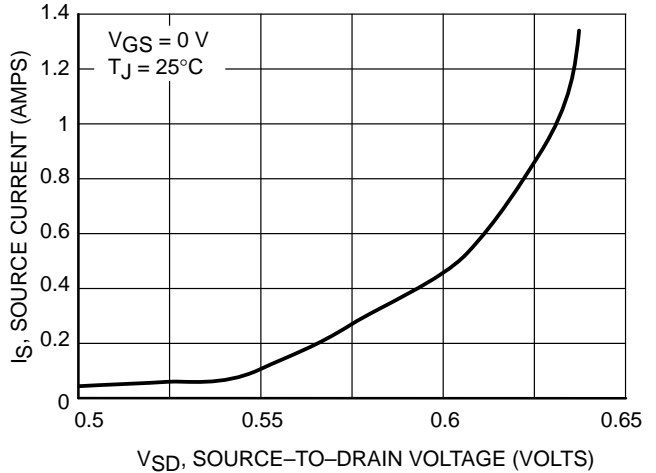


Figure 10. Diode Forward Voltage versus Current

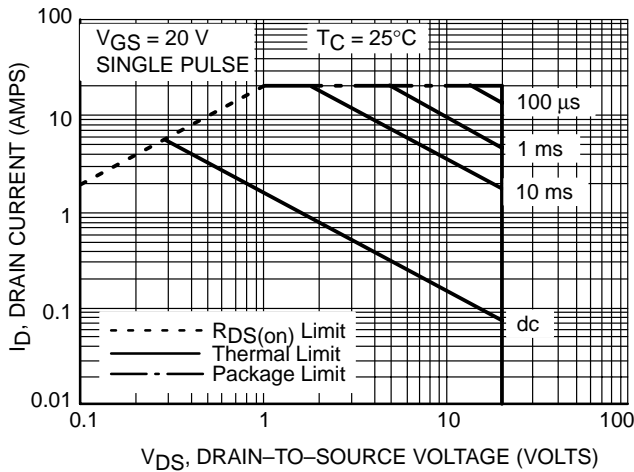


Figure 11. Maximum Rated Forward Biased Safe Operating Area

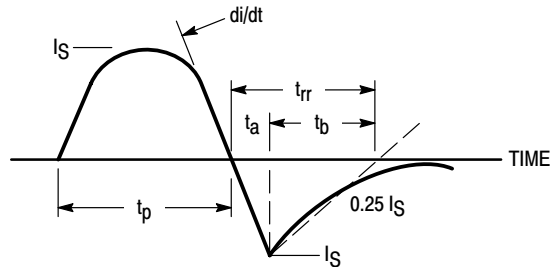


Figure 12. Diode Reverse Recovery Waveform

NTQD6968

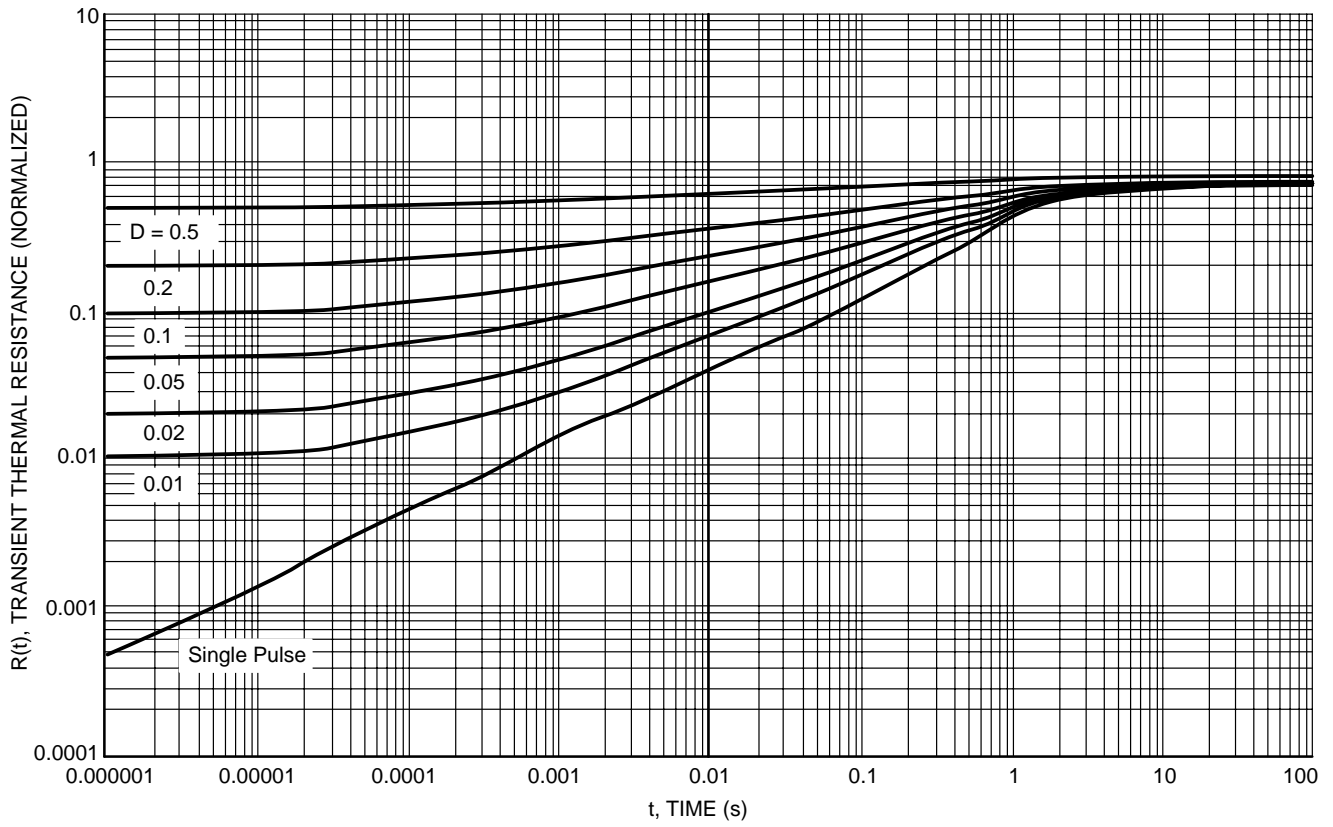


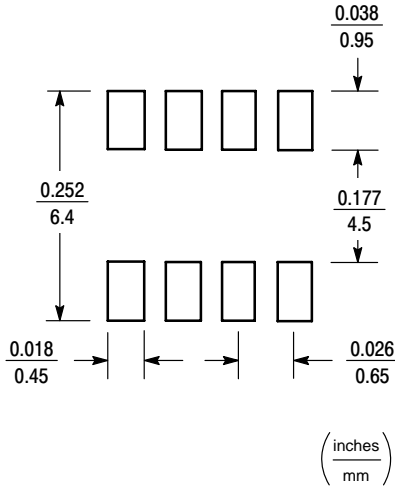
Figure 13. Thermal Response

INFORMATION FOR USING THE TSSOP-8 SURFACE MOUNT PACKAGE

RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to ensure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.

- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

* * Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

* * Due to shadowing and the inability to set the wave height to incorporate other surface mount components, the D²PAK is not recommended for wave soldering.

TYPICAL SOLDER HEATING PROFILE

For any given circuit board, there will be a group of control settings that will give the desired heat pattern. The operator must set temperatures for several heating zones, and a figure for belt speed. Taken together, these control settings make up a heating “profile” for that particular circuit board. On machines controlled by a computer, the computer remembers these profiles from one operating session to the next. Figure 14 shows a typical heating profile for use when soldering a surface mount device to a printed circuit board. This profile will vary among soldering systems but it is a good starting point. Factors that can affect the profile include the type of soldering system in use, density and types of components on the board, type of solder used, and the type of board or substrate material being used. This profile shows temperature versus time.

The line on the graph shows the actual temperature that might be experienced on the surface of a test board at or near a central solder joint. The two profiles are based on a high density and a low density board. The Vitronics SMD310 convection/infrared reflow soldering system was used to generate this profile. The type of solder used was 62/36/2 Tin Lead Silver with a melting point between 177–189°C. When this type of furnace is used for solder reflow work, the circuit boards and solder joints tend to heat first. The components on the board are then heated by conduction. The circuit board, because it has a large surface area, absorbs the thermal energy more efficiently, then distributes this energy to the components. Because of this effect, the main body of a component may be up to 30 degrees cooler than the adjacent solder joint.

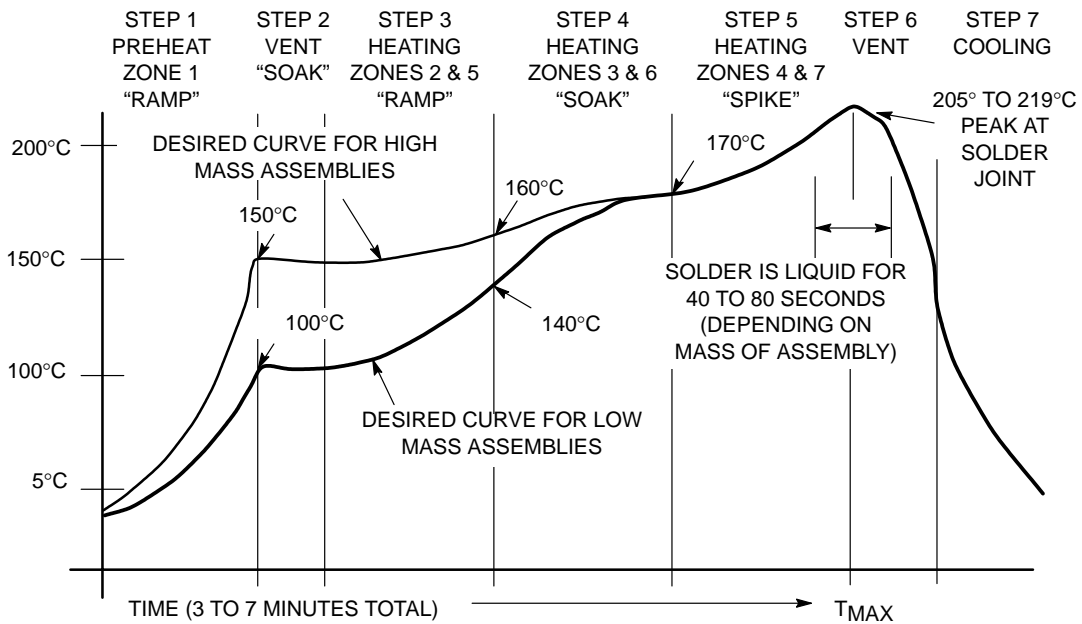
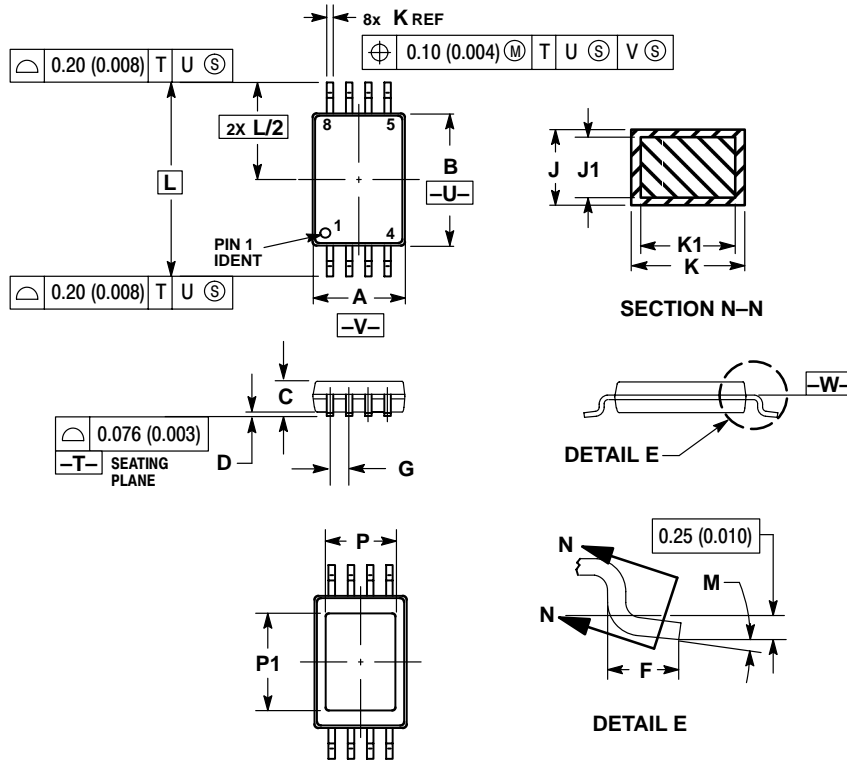


Figure 14. Typical Solder Heating Profile

NTQD6968

PACKAGE DIMENSIONS

TSSOP-8
CASE 948S-01
PLASTIC
ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	4.30	4.50	0.169	0.177
C	---	1.10	---	0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.70	0.020	0.028
G	0.65 BSC		0.026 BSC	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°
P	---	2.20	---	0.087
P1	---	3.20	---	0.126

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center
4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.